

考試規則：

- Close book。可以使用計算機，但不能用手機或其他電子產品。請關閉手機。
- 考試時間: 13:20~15:10
- 沒有過程不給分 (題目未說明解題方式者，皆用小信號模型參數表示)

Q1: (15%)

請寫出 V_{out}/V_{in} 的等效開迴路增益(A_{OL})、回授因子(Feedback factor, β)與閉迴路增益(A_{CL})。(15%)

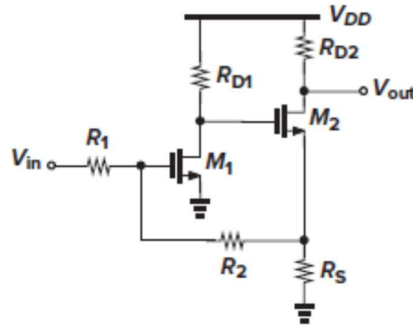


Fig. 1

Q2: (20%)

Suppose the open-loop transfer function of a two-stage op-amp is expressed as

$$H_{open}(s) = \frac{A_0 \left(1 + \frac{s}{\omega_z}\right)}{\left(1 + \frac{s}{\omega_{p1}}\right) \left(1 + \frac{s}{\omega_{p2}}\right)}$$

(a) 假如 $\omega_{p2} = A_0 \omega_{p1}$ and $\omega_z = 10 \omega_{p2}$ ，請畫出 $H_{open}(s)$'s bode plots for Magnitude and phase 並標示出 unit-gain frequency $\omega_u = ?$ Phase Margin (PM) 是多少? (10%)

(b) 一般的Two-Stage Opamp中，使用Miller電容跨接在第二級電路，其目的為何? 請解釋之。(10%)

Q3: (20%)

假設 Fig. 3 是一個 nMOST，畫出來的電晶體模型為 C_{ox} 、通道寬度(W)、長度(L)與 Diffusion 寬度(E)。

(a) 請簡單解釋 Fig. 3(b)中的 C_1 - C_6 ，其中 C_5 與 C_6 要用 C_j and C_{jsw} 表示。(10%)

(b) 寫出 Fig. 3(a)中， C_{GS} , C_{GD} , C_{DB} , C_{SB} ，分別以 C_1 - C_6 表示。(5%)

(c) 根據 Fig. 3(a)的小訊號模型(操作在飽和區)，簡單說明五個電容與其跨壓的關係(有關或無關)。(5%)

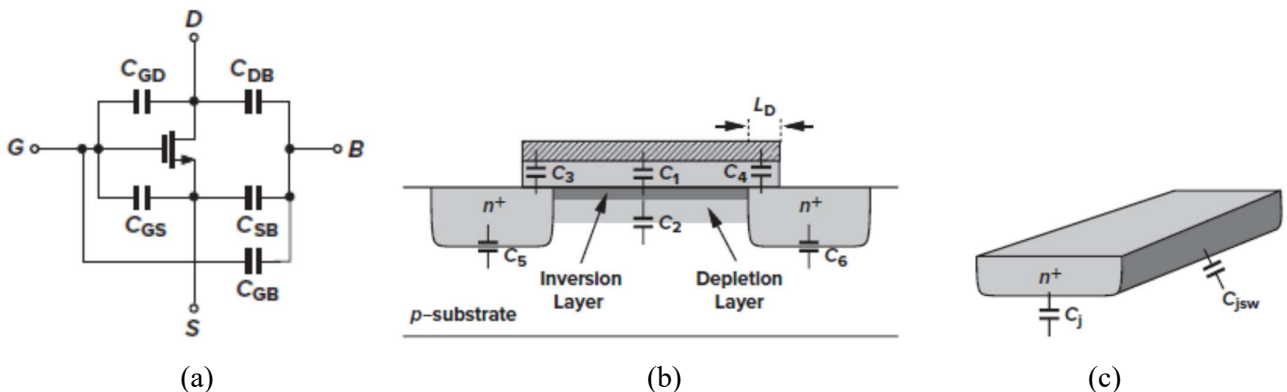


Fig. 3

Q4: (20%)

(a) 在 Fig. 4(a) 中，請寫出此電路的輸入輸出轉換特性曲線與電壓增益(用小信號模型參數表示)。(10%)

(b) 在 Fig. 4(b) 中，請寫出此電路的輸入輸出轉換特性曲線與電壓增益(用小信號模型參數表示)。(10%)

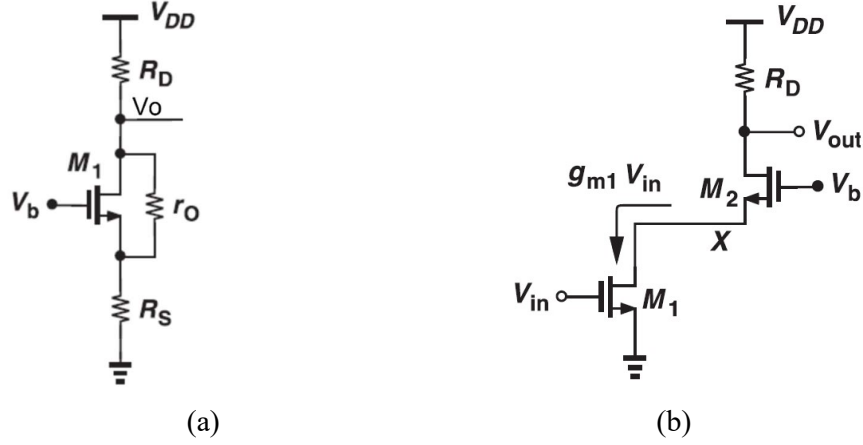


Fig. 4

Q5: (10%)

假設 Fig. 5 中的所有電晶體都操作在飽和區且 $\lambda \neq 0$ ，用小信號模型參數表示每個子電路中的小訊號差動增益 ($A_v = V_{out}/V_{in} > 0$)。

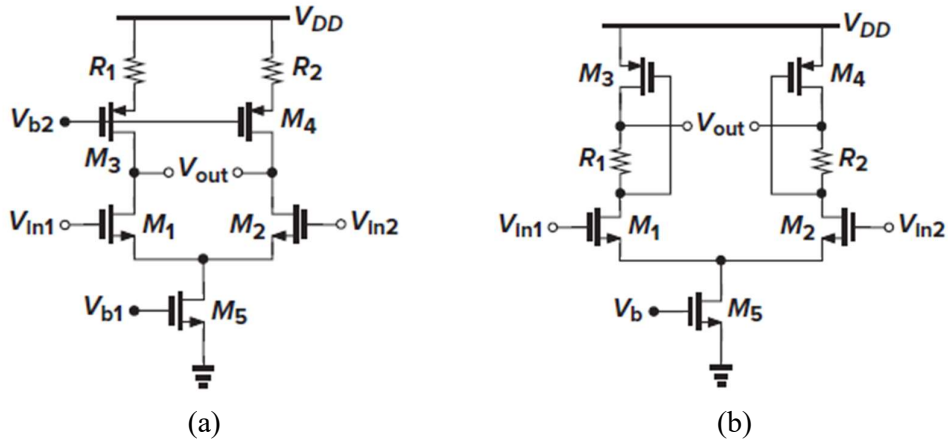


Fig. 5

Q6: (15%)

(a) 在 Fig. 6(a) 中，相對於其他兩個電流源產生電路，其主要缺點為何？請解釋之。(10%)

(b) 在 Fig. 6(c) 中，”M4與I1”的引入，其目的為何？應該如何設計？(5%)

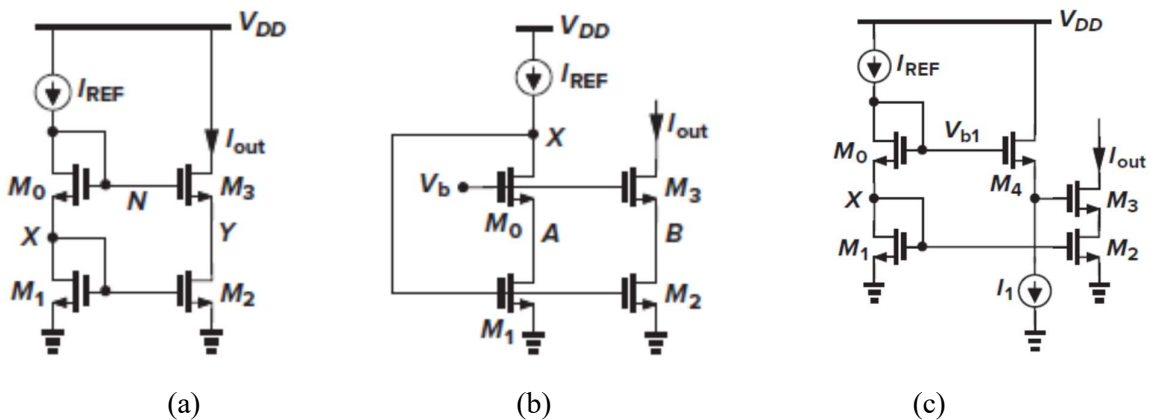
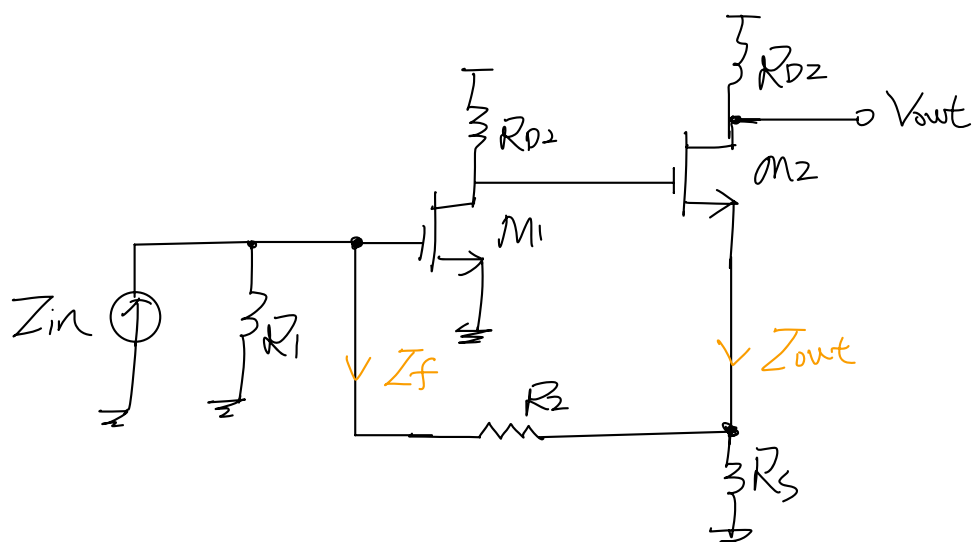
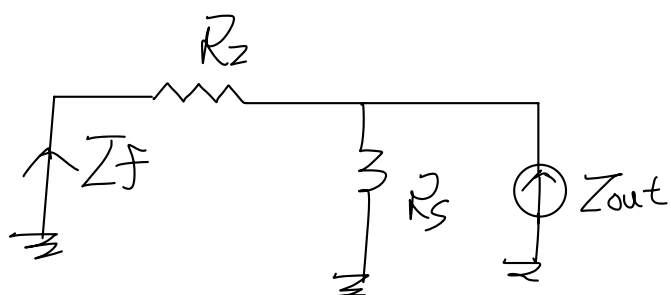


Fig. 6

Q₁ 2

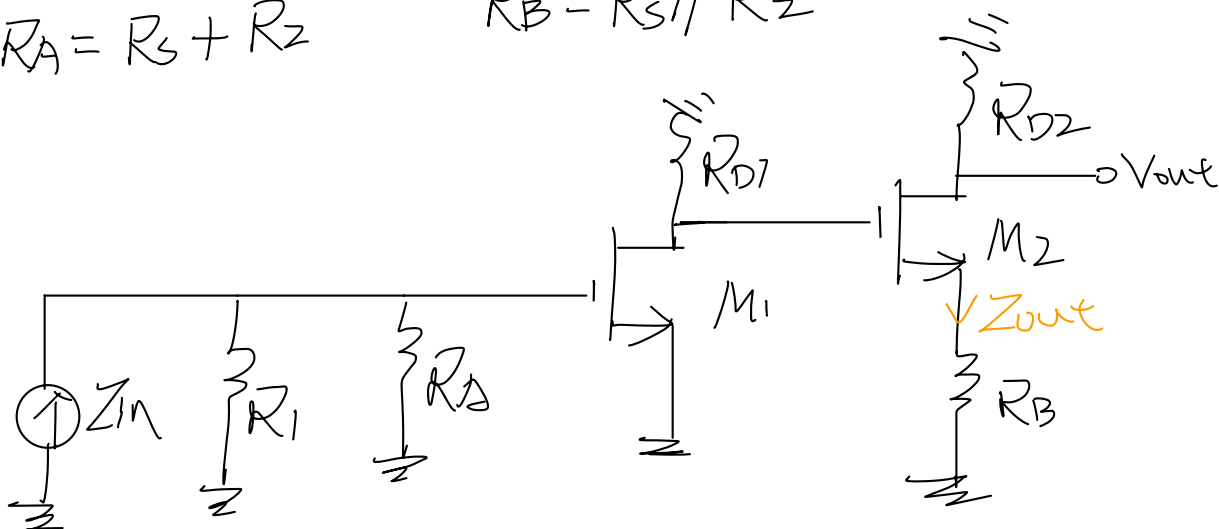


Z-I feedback



$$\beta_z = \frac{Z_f}{Z_{out}} = - \frac{R_s}{R_s + R_z} \neq$$

$$R_A = R_s + R_z \quad R_B = R_s \parallel R_z$$



$$V_{g2} = Z_{in} (R_1 \parallel R_A) \times (-g_{m1} R_{D1})$$

$$I_{out} = G_{m2} V_{g2} = \frac{g_{m2} r_{o2}}{r_{o2} + (1 + g_{m2}' r_{o2}) R_B}$$

$$g_{m2}' = g_{m2} + g_{m2b}$$

$$A_{Z,OL} = \frac{I_{out}}{I_{in}} = -g_{m1} R_{D1} \times G_{m2} \times (R_1 \parallel R_A)$$

$$\beta_Z A_{Z,OL} = g_{m1} R_{D1} \times G_{m2} \times (R_1 \parallel R_A) \times \frac{R_S}{R_S + R_2}$$

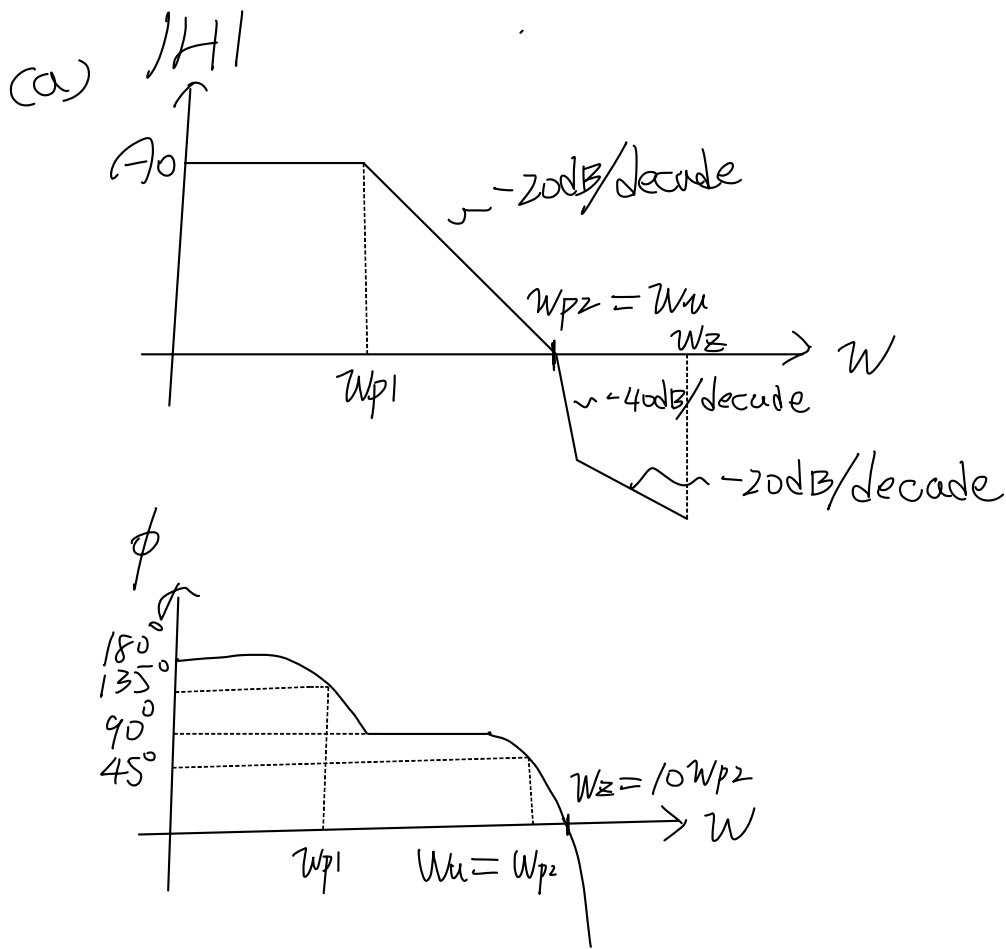
$$\Rightarrow A_{Z,CL} = \frac{A_{Z,OL}}{1 + \beta_Z A_{Z,OL}} = \frac{-g_{m1} R_{D1} \times G_{m2} \times (R_1 \parallel R_A)}{1 + g_{m1} R_{D1} \times G_{m2} \times (R_1 \parallel R_A) \times \frac{R_S}{R_S + R_2}}$$

Assume $\beta_Z A_{Z,OL} \gg 1$

$$\Rightarrow A_{Z,CL} \approx \frac{R_S + R_2}{R_S} = 1 + \frac{R_2}{R_S}$$

$$\Rightarrow A_{v,CL} = A_{Z,CL} \times \frac{R_{D2}}{R_1} = \left(1 + \frac{R_2}{R_S}\right) \frac{R_{D2}}{R_1} \neq$$

Q2



$$PM = 180^\circ - \tan^{-1}\left(\frac{\omega_u}{\omega_{p1}}\right) - \tan^{-1}\left(\frac{\omega_u}{\omega_{p2}}\right) - \tan^{-1}\left(\frac{\omega_u}{\omega_z}\right)$$

$$= 180^\circ - \tan^{-1}(A_0) - \tan^{-1}(1) - \tan^{-1}(0.1)$$

$$\approx 180^\circ - 90^\circ - 45^\circ - 0 = 45^\circ \quad \#$$

或

$$PM = 180^\circ - 90^\circ - 45^\circ - 5.7^\circ \approx 39.3^\circ \quad \#$$

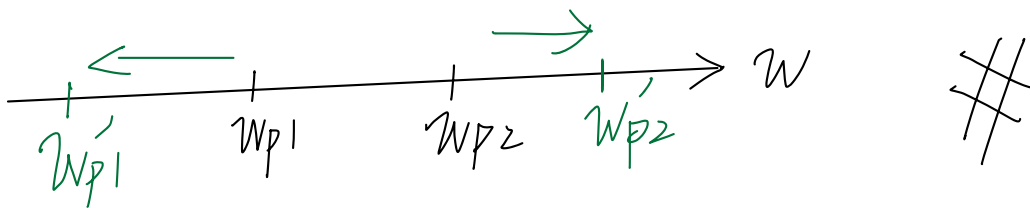
(b)

如果沒有使用 Miller Compensation 的話

會使得 ω_{p1} 及 ω_{p2} 過於靠近，使得 PM 很差

因此透過 Miller Compensation 的技術

將 ω_{p1} 及 ω_{p2} 分離，使得 PM 變好!!



Q3

(a)

$C_1 = WL C_{ox}$ 表示 poly gate 與 oxide 間的氧化層電容

$C_2 = WL \sqrt{\frac{2\epsilon_s N_{sub}}{4\phi_f}}$ 表示 channel 與 substrate 間的空乏電容 送分!!

$$C_3, C_4 = WL_D C_{ox} = W C_{ov}$$

表示 poly gate 與 s/d 間的 overlap 氧化層電容

C_5, C_6 由 C_{js} 及 C_{jsw} 共同組成的空乏電容

$$\left. \begin{aligned} C_5 &= A_s C_{js} + P_s C_{jsw} \\ C_6 &= A_D C_{js} + P_D C_{jsw} \end{aligned} \right\} \begin{aligned} &\text{其中 } A = E \times W \\ &P = 2(W + E) \\ &\text{或 } P = (W + 2E) \end{aligned}$$

(b)

Assume 為飽和區

$$C_{GS} = C_3 + \frac{2}{3} C_1$$

$$C_{GD} = C_4$$

$$C_{SB} = C_5$$

$$C_{DB} = C_6 \quad \#$$

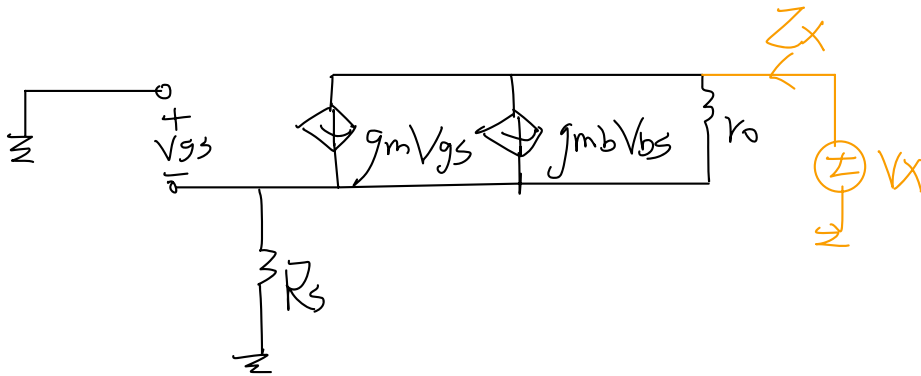
(c)

C_{GS}/C_{DB} C_{SB} 与电压有关

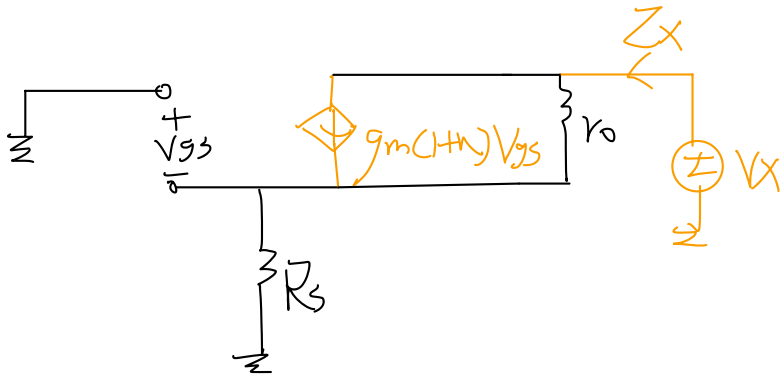
C_{GB}/C_{GD} 与电压无关 $\#$

Q4

(a)



$$V_{BS} = V_{GS} \Rightarrow (g_m + g_{mb}) V_{GS} = (1 + \mu) g_m V_{GS}$$



$$V_{GS} = 0 - Z_X R_S = -Z_X R_S$$

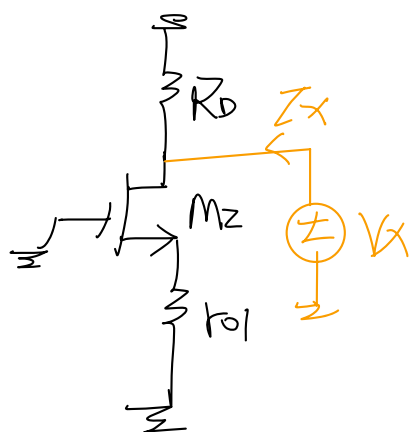
$$V_X = Z_X R_S + Z_X [(1 + \mu) g_m R_S + 1] r_o$$

$$R_{out}' = \frac{V_X}{I_X} = R_S + [(1 + \mu) g_m R_S + 1] r_o$$

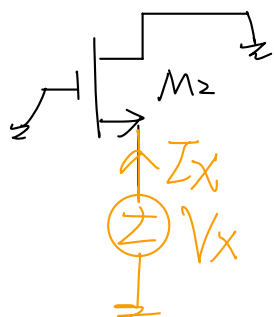
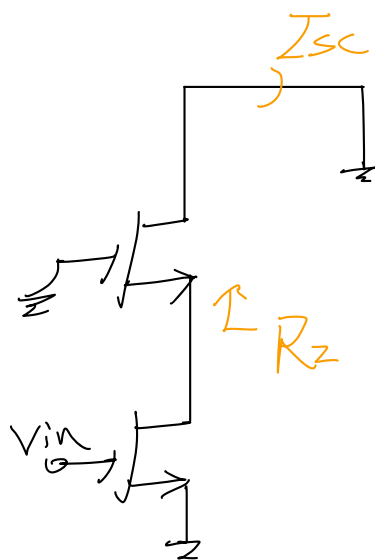
$$\text{or } R_{out}' = r_o + [(1 + \mu) g_m r_o + 1] R_S$$

$$R_{out} = R_D \parallel R_{out}' \quad \#$$

(b)



$$R_{out} = R_D \parallel \left\{ r_{o2} + [1 + (g_{m2} + g_{m2b})r_{o2}]r_{o1} \right\}$$



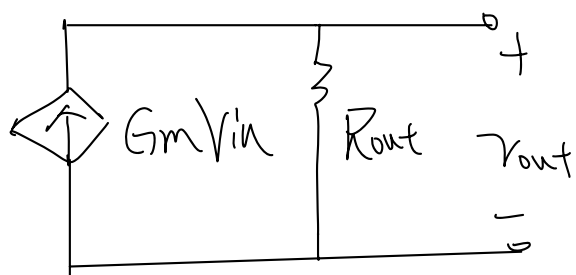
$$I_X = (g_{m2} + g_{m2b})V_X + \frac{V_X}{r_{o2}}$$

$$\Rightarrow R_Z = \frac{V_X}{I_X} = \frac{1}{g_{m2} + g_{m2b} + \frac{1}{r_{o2}}}$$

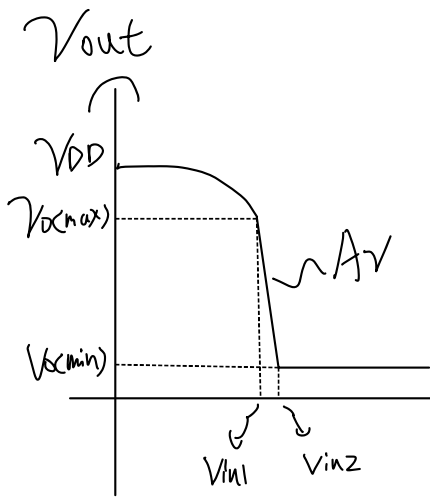
$$\text{或 } R_Z = \frac{r_{o2}}{1 + (g_{m2} + g_{m2b})r_{o2}}$$

$$I_{sc} = -g_{m1}V_{in} \frac{r_{o1}}{r_{o1} + R_Z} = -g_{m1} \frac{r_{o1}[1 + (g_{m2} + g_{m2b})r_{o2}]}{r_{o1} + r_{o2} + (g_{m2} + g_{m2b})r_{o2}r_{o1}} V_{in}$$

$$G_m = \frac{I_{sc}}{V_{in}} = -g_{m1} \frac{r_{o1}}{r_{o1} + R_Z} = -g_{m1} \frac{r_{o1}[1 + (g_{m2} + g_{m2b})r_{o2}]}{r_{o1} + r_{o2} + (g_{m2} + g_{m2b})r_{o2}r_{o1}} \stackrel{(r_{o1} \gg R_Z)}{\approx} -g_{m1}$$



$$A_v = G_m R_{out} \neq \#$$



$$V_{in1} = V_{th1}$$

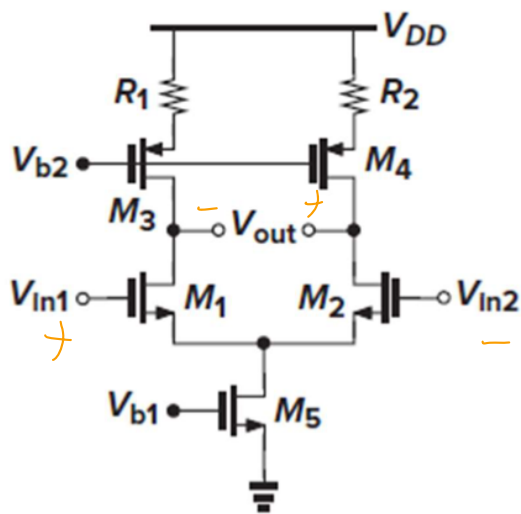
$$V_{in2} = V_b - V_{GS2} + V_{th1}$$

$$V_{out(max)} = V_{DD} - \overbrace{G_m(V_{in1})}^{\text{大訊号的 } G_m} V_{in1} R_D$$

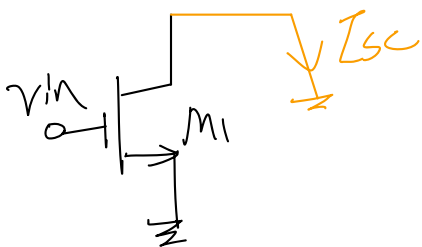
$$V_{out(min)} = V_b - V_{th2}$$



a.

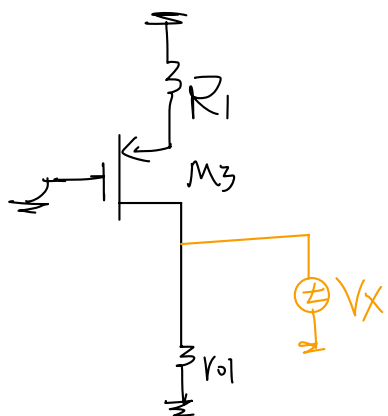


$$v_{in} = v_{in1} - v_{in2}$$



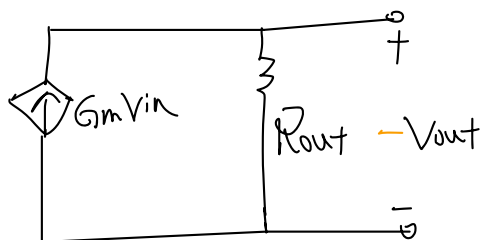
$$Z_{sc} = -j\omega L$$

$$G_m = \frac{I_{sc}}{V_{in}} = -g_m$$



$$R_{op} = R_{o3} + [1 + (g_{m3} + g_{m3b}) R_{o3}] R_1$$

$$R_{out} = R_{o1} \parallel R_{oP}$$

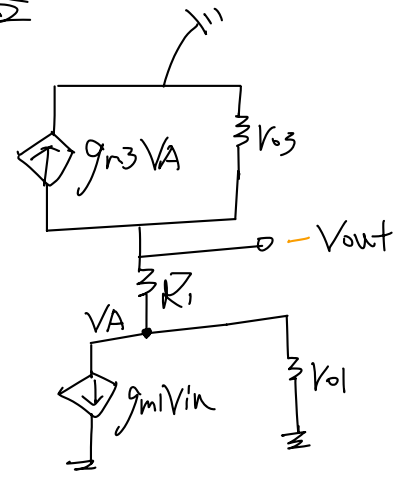
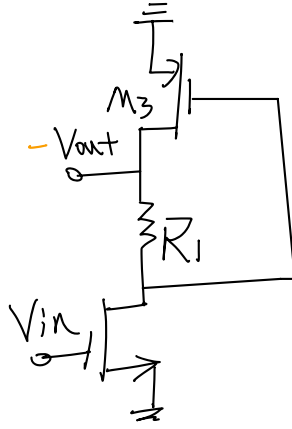
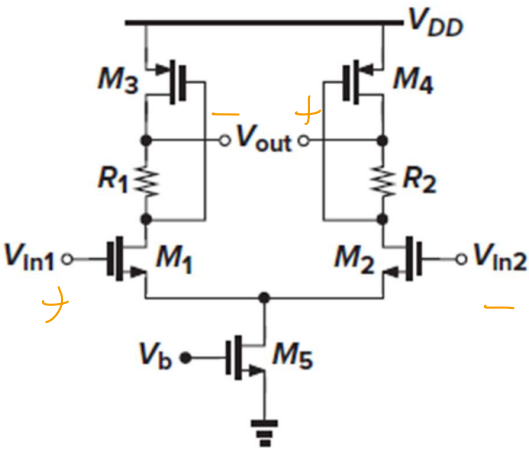


$$-\frac{V_{out}}{V_{in}} = G_m R_{out}$$

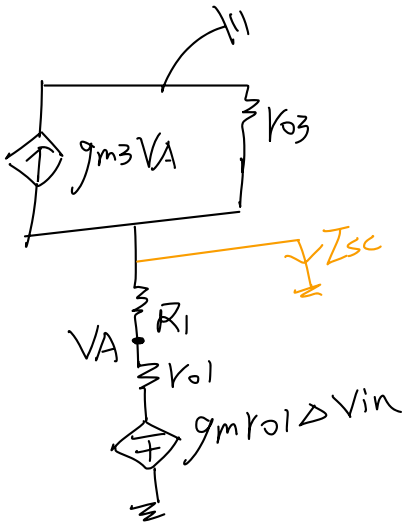
$$\frac{V_{out}}{V_{in}} = -G_m R_{out} \quad \#$$

b.

利用差模等效半电路



假设 $V_{in} = V_{in1} - V_{in2}$

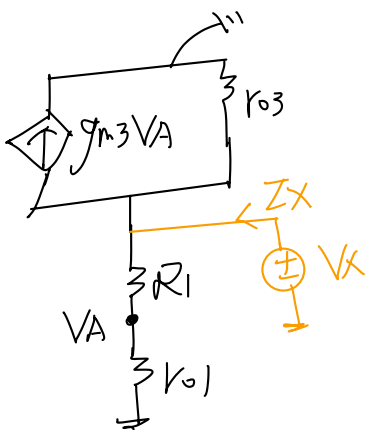


$$V_A = -g_{m1} R_{01} V_{in} \frac{R_1}{R_{01} + R_1}$$

$$I_{sc} = - \left[\frac{g_{m1} R_{01}}{R_1 + R_{01}} - g_{m3} g_{m1} R_{01} \frac{R_1}{R_{01} + R_1} \right] V_{in}$$

$$\Rightarrow I_{sc} = \frac{-g_{m1} R_{01}}{R_1 + R_{01}} [1 - g_{m3} R_1] V_{in}$$

$$\Rightarrow G_m = \frac{I_{sc}}{V_{in}} = \frac{-g_{m1} R_{01}}{R_1 + R_{01}} [1 - g_{m3} R_1]$$

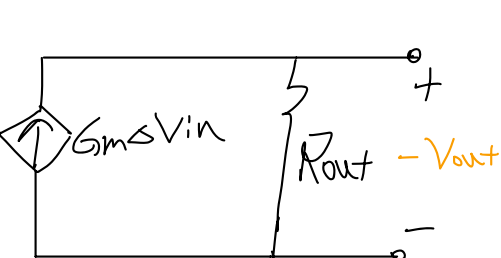


$$V_A = \frac{R_{01}}{R_1 + R_{01}} V_X$$

$$I_X = \left(\frac{1}{R_1 + R_{01}} + \frac{1}{R_{03}} + \frac{g_{m3} R_{01}}{R_1 + R_{01}} \right) V_X$$

$$\Rightarrow I_X = \left(\frac{1 + g_{m3} R_{01}}{R_1 + R_{01}} + \frac{1}{R_{03}} \right) V_X$$

$$\Rightarrow R_{out} = \frac{V_X}{I_X} = \frac{R_1 + R_{01}}{1 + g_{m3} R_{01}} \parallel R_{03}$$



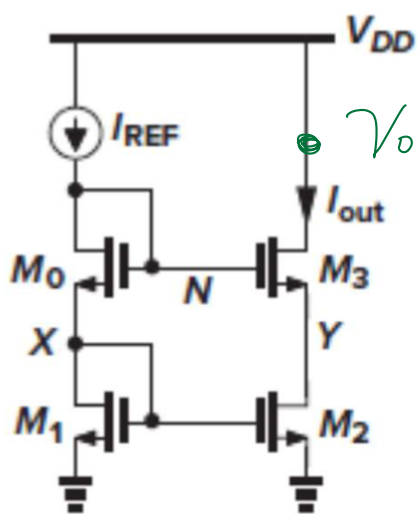
$$\frac{-V_{out}}{V_{in}} = G_m R_{out}$$

$$\Rightarrow \frac{V_{out}}{V_{in}} = -G_m R_{out} = \frac{g_{m1} R_{01} R_{03} (1 - g_{m3} R_1)}{R_1 + R_{03} + (1 + g_{m3} R_{03}) R_{01}} \neq$$

Q6

a.

Fig 6(a) 相比 (b) 及 (c) 所需的 V_{ocmin} 較大



(a)

$$V_{ocmin} = V_{GS1} + V_{GS0} - V_{th3}$$

$$= 2V_{ov} + V_{th}$$

而 (b), (c)

$$V_{ocmin} = 2V_{ov}$$

#

(b)

透過加入 M_4 及 Z 來當作 level-shift
並且設計 M_4 具有較大的 (W/L) 使得 V_{ov4} 極小

$$\text{讓 } V_{GS4} \approx V_{th4}$$

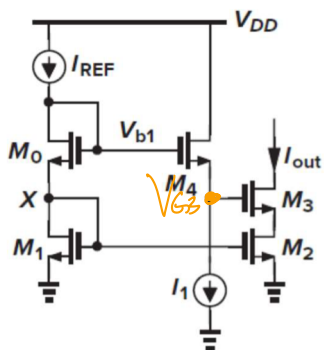
$$V_{ocmin} = V_{GS1} + V_{GS0} - V_{GS4} - V_{th3}$$

$$\approx V_{GS1} + V_{GS0} - V_{th4} - V_{th3}$$

$$= 2V_{ov}$$

得到較小的 V_{ocmin}

#



(c)